

ABSTRACT

A manufacturing method, and an integrated circuit resulting therefrom, has a substrate and a semiconductor device thereon. A stop layer over the substrate has a first dielectric layer formed thereon having an opening into which a first conformal barrier is formed. A first
5 conformal barrier liner is formed in the opening, processed, and treated to improve adhesion. Portions of the first conformal barrier liner on the sidewalls act as a barrier to diffusion of conductor core material to the first dielectric layer. A conductor material is formed in the opening over the vertical portions of the first conformal barrier liner and the first stop layer.